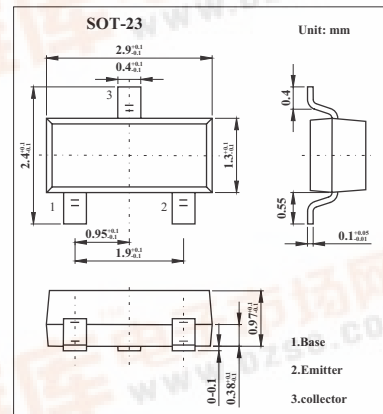


SMD Type Transistors

Silicon PNP Epitaxial  
2SB831

Features

- Low frequency amplifier.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V <sub>CB0</sub>	-25	V
Collector to emitter voltage	V <sub>CEO</sub>	-20	V
Emitter to base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-0.7	A
peak collector current	I <sub>CP</sub>	1	A
Collector power dissipation	P <sub>C</sub>	150	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0	-25			V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -1 mA, R <sub>BE</sub> = ∞	-20			V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -10 μA, I <sub>C</sub> = 0	-5			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = -20 V, I <sub>E</sub> = 0			-1	mA
DC current transfer ratio *	h <sub>FE</sub>	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -0.15 A	85		240	
Collector to emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>C</sub> = -0.5 A, I <sub>B</sub> = -0.05 A			-0.5	V
Base to emitter voltage *	V <sub>BE</sub>	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -0.15 A			-1	V

\* Pulse test.

hFE Classification

Marking	BB	BC
hFE	85~170	120~240

